



VOIDLESS HERMETICALLY SEALED SWITCHING DIODES

Qualified per MIL-PRF-19500/578

DESCRIPTION

This popular surface mount equivalent JEDEC registered switching/signal diodes are military qualified and available with internal metallurgical bonded construction. These small low capacitance diodes with very fast switching speeds are hermetically sealed and bonded into a "D-5D" package. They may be used in a variety of fast switching applications including computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, as well as decoding or encoding applications, etc. Microsemi also offers a variety of other switching/signal diodes.

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- JEDEC registered surface mount equivalents of 1N6638, 1N6642, and 1N6643.
- Ultra fast recovery time.
- Very low capacitance.
- Metallurgically bonded.
- Non-cavity glass package.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/578.
- Replacements for 1N4148UR, 1N4148UR-1, 1N4150UR-1, and 1N914UR.
- RoHS compliant devices available (commercial grade only).

APPLICATIONS / BENEFITS

• Small size for high density mounting (see package illustration).

Ideal for: High frequency data lines RS-232 & RS–422 Interface Networks Ethernet: 10 Base T Switching core drivers LAN

Computers

MAXIMUM RATINGS @ T_A = +25 °C unless otherwise noted.

Parameters/Test Conditions	Symbol	Value	Unit	
Junction and Storage Temp	T_J and T_{STG}	-65 to +175	°C	
Thermal Resistance Junction-to-End	R _{ejec}	40	°C/W	
Thermal Resistance Junction-to-Amb	R _{eja}	250	°C/W	
Peak Forward Surge Current @ T _A =	I _{FSM}	2.5	А	
(Test pulse = 8.3 ms, half-sine wave.				
Average Rectified Forward Current @	lo	300	mA	
(Derate at 4.6 mA/°C Above T_{EC} = +				
Breakdown Voltage: 1N6638US		V _{BR}	150	V
	1N6642US		100	
	1N6643US		75	
Working Peak Reverse Voltage:	1N6638US	V _{RWM}	125	V
	1N6642US		75	
	1N6643US		50	

NOTES: 1. T_A = +75 °C on printed circuit board (PCB), PCB = FR4 - .0625 inch (1.59 mm) 1-layer 1-Oz Cu, horizontal, in still air; pads for US = .061 inch (1.55 mm) x .105 inch (2.67 mm); R_{OJA} with a defined PCB thermal resistance condition included, is measured at I_o = 300 mA.

<u>Qualified Levels</u>: JAN, JANTX, JANTXV and JANS



"D" SQ-MELF (D-5D) Package

Also available in:

"D" Package (axial-leaded) 1N6638 42 43

MSC – Lawrence

6 Lake Street, Lawrence, MA 01841 1-800-446-1158 Tel: (978) 620-2600 Fax: (978) 689-0803

MSC – Ireland

Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

Website:

www.microsemi.com



RoHS Compliance

e3 = RoHS compliant (available

on commercial grade only)

Surface Mount Package

Blank = non-RoHS compliant



MECHANICAL and PACKAGING

- CASE: Voidless hermetically sealed hard glass.
- TERMINALS: Tin-Lead plate with >3% Lead. Solder dip is available upon request.
- MARKING: Body painted and alpha numeric.
- POLARITY: Cathode indicated by band.
- Tape & Reel option: Standard per EIA-481-1-A with 12 mm tape. Consult factory for quantities.
- See <u>Package Dimensions</u> on last page.

PART NOMENCLATURE

US

(e3)

1N6638



JEDEC type number

See <u>Electrical Characteristics</u> table

SYMBOLS & DEFINITIONS					
Symbol	Definition				
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.				
V _{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.				
V_{F}	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.				
I _R	Maximum Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.				
С	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage.				
t _{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified recovery decay point after a peak reverse current is reached.				

ELECTRICAL CHARACTERISTICS @ 25°C unless otherwise noted.

MAXIMUM FORWARD VOLTAGE V _F @ I _F NUMBER		VARD	MAXIMUM DC REVERSE CURRENT			REVERSE RECOVERY TIME t _{rr} (Note 1)	RECOVERY VOLTAGE AND TIME		MAXIMUM JUNCTION CAPACITANCE f = 1 MHz Vsig = 50 mV		
			Ι _{R1} V _R = 20 V	I _{R2} V _R =V _{RWM}	I _{R3} V _R =20 V T _A = +150 °C	I _{R4} V _R =V _{RWM} T _A = +150 °C	-	I _F =200m/	A, t _r =1ns t _{fr}	(p V _R =0 V	р-р) V _R =1.5 V
	V @ mA	V @ mA	nA	nA	μA	μA	ns	v	ns	pf	pf
1N6638US	0.8 V @ 10 mA	1.1 V @ 200 mA	35	500	50	100	4.5	5.0	20	2.5	2.0
1N6642US	0.8 V @ 10 mA	1.2 V @ 100 mA	25	500	50	100	5.0	5.0	20	5.0	2.8
1N6643US	0.8 V @ 10 mA	1.2 V @ 100 mA	50	500	75	100	6.0	5.0	20	5.0	2.8

NOTE: 1. Reverse Recovery Time Test Conditions – I_F=I_R=10 mA, I_{R(REC)} = 1.0 mA, C=3 pF, R_L = 100 ohms.



GRAPHS



Time (s)

FIGURE 2 <u>Maximum Thermal Impedance at $T_A = 55 \degree C$ </u>



GRAPHS (continued)



FIGURE 3 Maximum Thermal Impedance at T_{EC} = 25 °C



1N6638US, 1N6642US, 1N6643US

PACKAGE DIMENSIONS





	IN	СН	MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
BD	0.070	0.085	1.78	2.16		
ECT	0.019	0.028	0.48	0.71		
BL	0.165	0.195	4.19	4.95		
S	0.003	3 MIN.	0.08 MIN.			

NOTES:

- 1. Dimensions are in inches. Millimeters are given for general information only.
- 2. Dimensions are pre-solder dip.
- 3. U-suffix parts are structurally identical to the US-suffix parts.
 4. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.